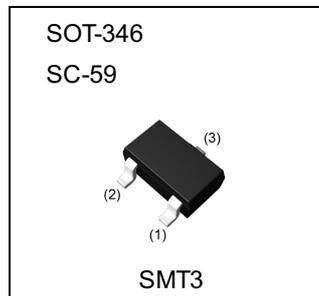


Parameter	Value
V_{CEO}	11V
I_C	50mA

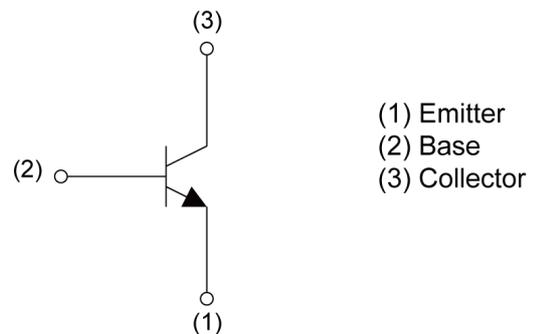
●Outline



●Features

- 1)High transition frequency.(Typ. $f_T=3.2\text{GHz}$)
- 2)Small $r_{bb'} \cdot C_c$ and high gain.(Typ.4ps)
- 3)Small NF.

●Inner circuit



●Application

UHF FREQUENCY CONVERTER, LOCAL OSCILLATOR

●Packaging specifications

Part No.	Package	Package size	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit.(pcs)	Marking
2SC3838K	SOT-346 (SMT3)	2928	T146	180	8	3000	AD

●Notice

This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.

● Absolute maximum ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Values	Unit
Collector-base voltage	V_{CBO}	20	V
Collector-emitter voltage	V_{CEO}	11	V
Emitter-base voltage	V_{EBO}	3	V
Collector current	I_C	50	mA
Power dissipation	P_D^{*1}	200	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Range of storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

● Electrical characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Collector-base breakdown voltage	BV_{CBO}	$I_C = 10\mu\text{A}$	20	-	-	V
Collector-emitter breakdown voltage	BV_{CEO}	$I_C = 1\text{mA}$	11	-	-	V
Emitter-base breakdown voltage	BV_{EBO}	$I_E = 10\mu\text{A}$	3	-	-	V
Collector cut-off current	I_{CBO}	$V_{CB} = 10\text{V}$	-	-	500	nA
Emitter cut-off current	I_{EBO}	$V_{EB} = 2\text{V}$	-	-	500	nA
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 10\text{mA}, I_B = 5\text{mA}$	-	-	500	mV
DC current gain	h_{FE}	$V_{CE} = 10\text{V}, I_C = 5\text{mA}$	56	-	270	-
Transition frequency	f_T	$V_{CE} = 10\text{V}, I_E = -10\text{mA}, f = 500\text{MHz}$	1.4	3.2	-	GHz
Output capacitance	C_{ob}	$V_{CB} = 10\text{V}, I_E = 0\text{A}, f = 1\text{MHz}$	-	0.8	1.5	pF
Noise figure	N_F	$V_{CB} = 6\text{V}, I_C = 2\text{mA}, f = 500\text{MHz}, R_g = 50\Omega$	-	3.5	-	dB

h_{FE} values are classified as follows :

rank	N	P	Q	-	-
h_{FE}	56-120	82-180	120-270	-	-

*1 Each terminal mounted on a reference land.

● Electrical characteristic curves ($T_a = 25^\circ\text{C}$)

Fig.1 Ground Emitter Propagation Characteristics

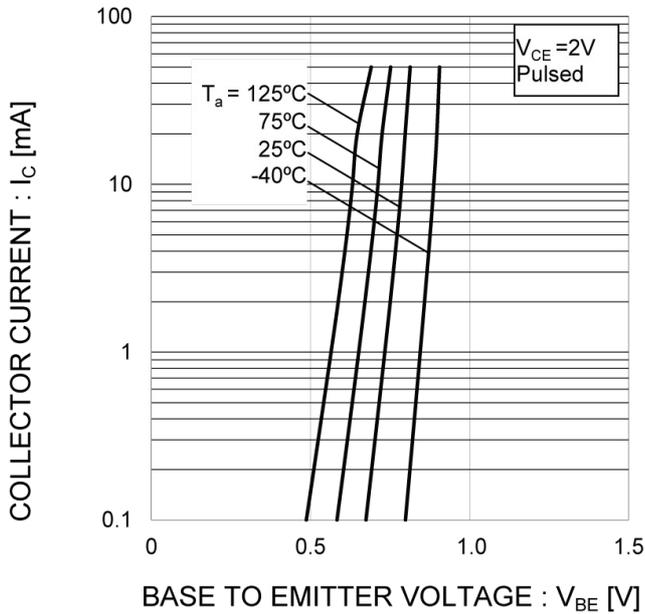


Fig.2 Typical Output Characteristics

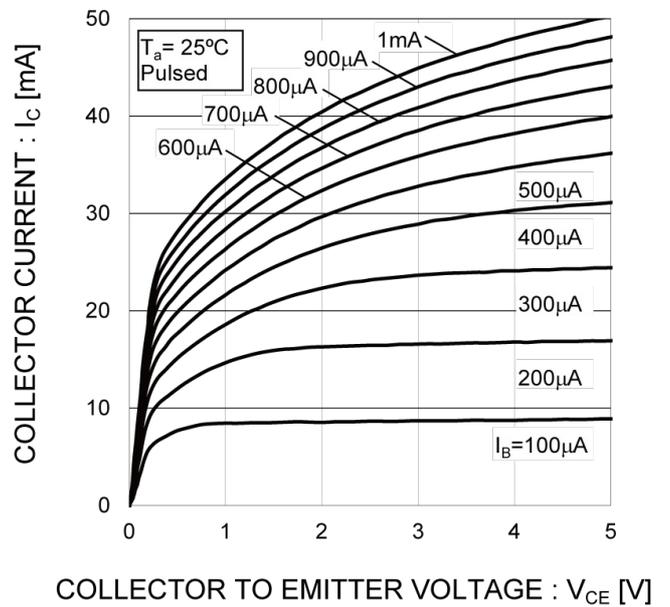


Fig.3 DC Current Gain vs. Collector Current (I)

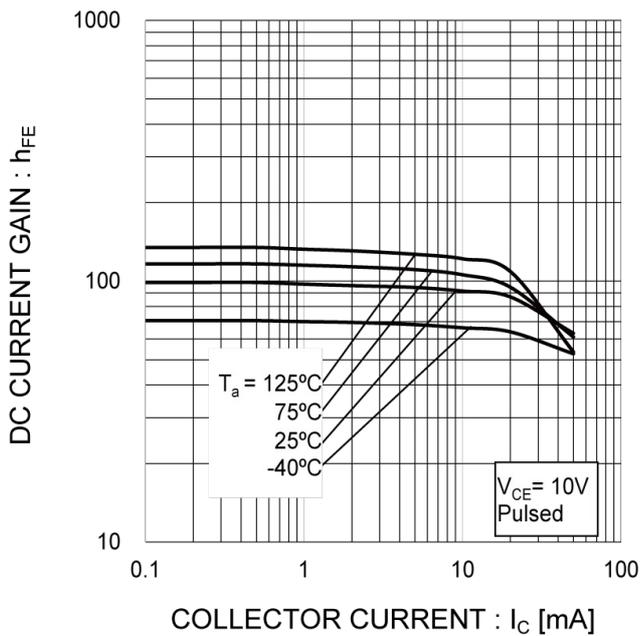
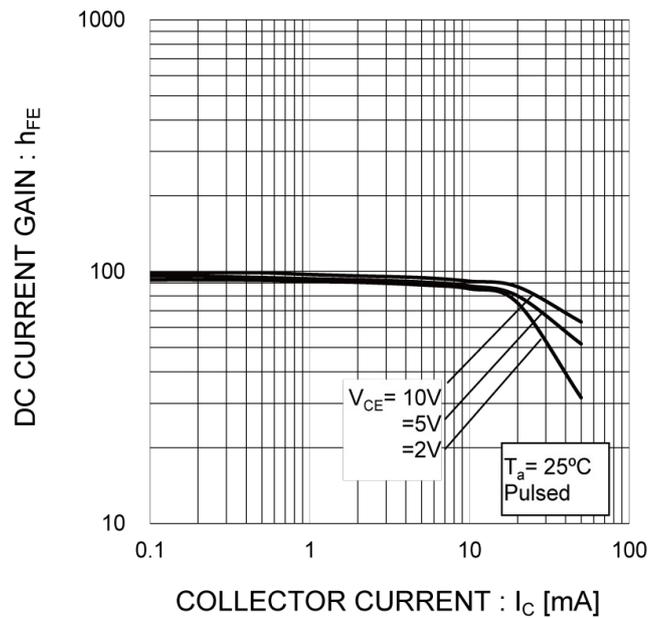


Fig.4 DC Current Gain vs. Collector Current (II)



● Electrical characteristic curves ($T_a = 25^\circ\text{C}$)

Fig.5 Collector to base time constance vs. collector current

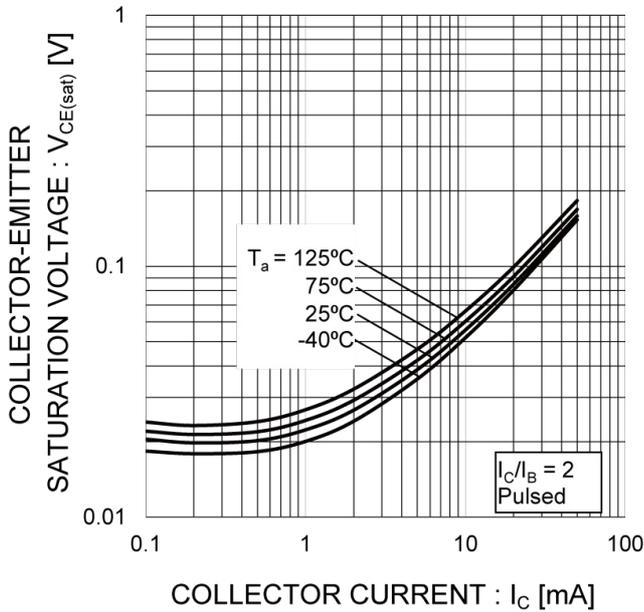


Fig.6 Collector-Emitter Saturation Voltage vs. Collector Current (II)

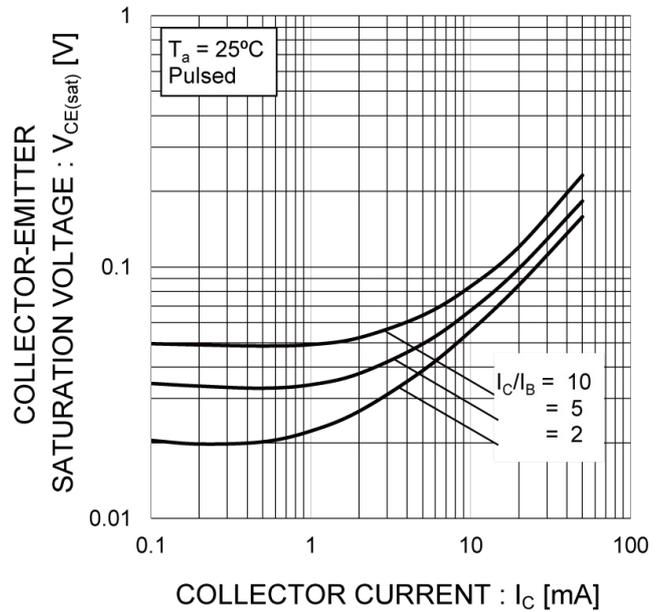


Fig.7 Base-Emitter Saturation Voltage vs. Collector Current

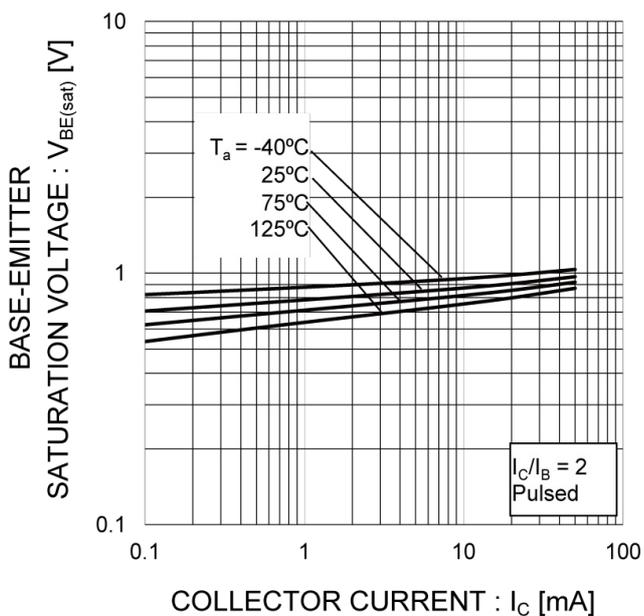
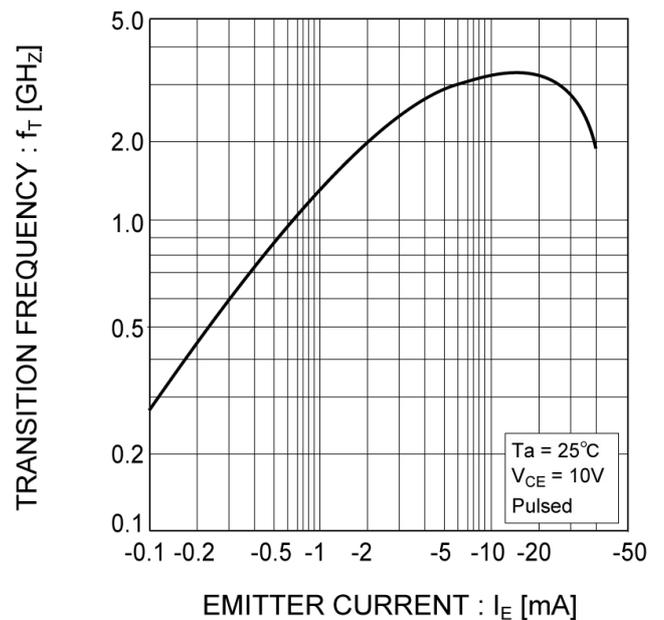


Fig.8 Gain Bandwidth Product vs. Emitter Current



● Electrical characteristic curves ($T_a = 25^\circ\text{C}$)

Fig.9 Capacitance vs. Reverse Bias Voltage

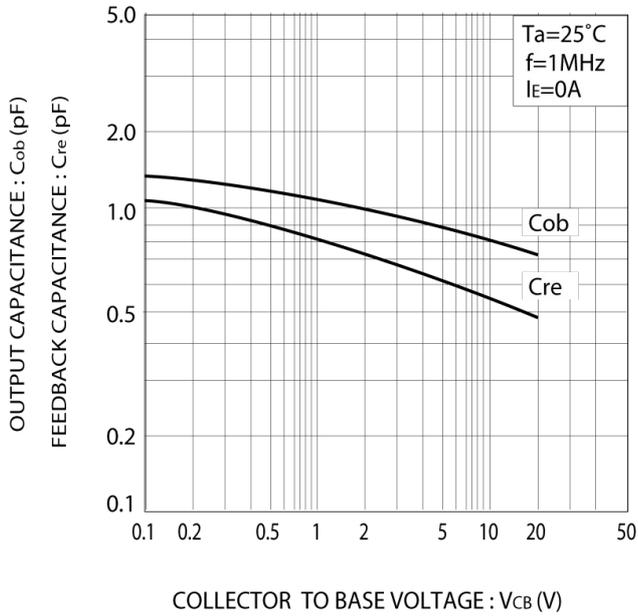


Fig.10 Collector to base time constant vs. collector current

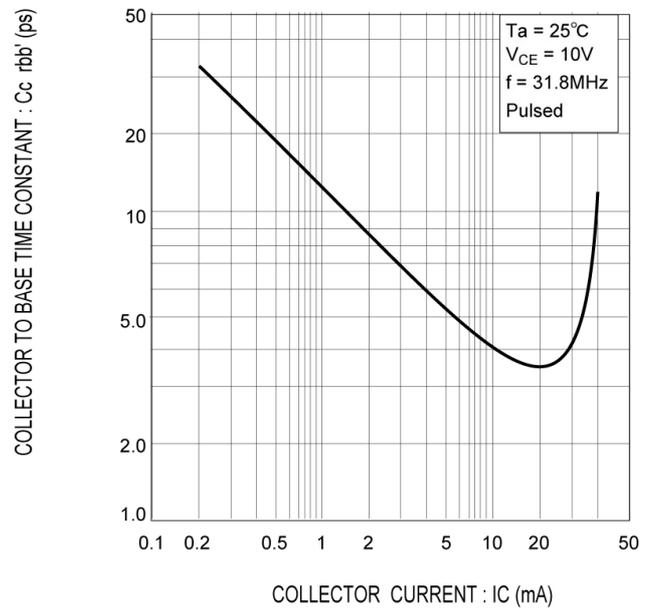
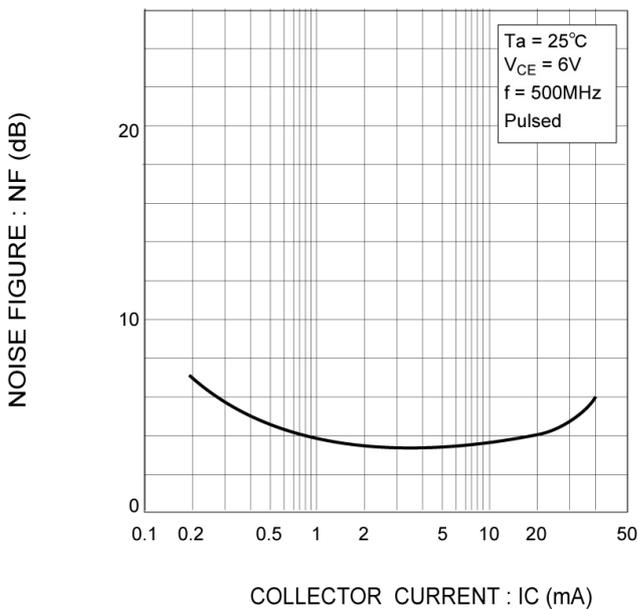
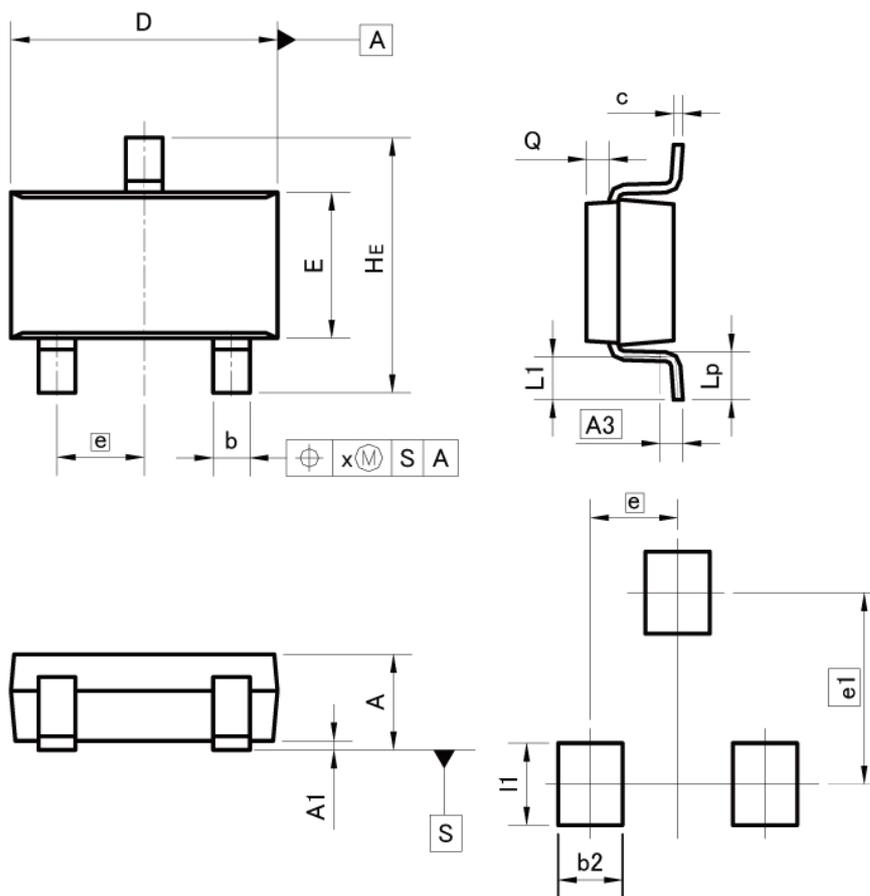


Fig.11 Noise factor vs. collector current characteristics



●Dimensions

SOT-346
SC-59
(SMT3)



Pattern of terminal position areas
[Not a pattern of soldering pads]

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.00	1.30	0.039	0.051
A1	0.00	0.10	0.000	0.004
A3	0.25		0.010	
b	0.35	0.50	0.014	0.020
c	0.09	0.25	0.004	0.010
D	2.80	3.00	0.110	0.118
E	1.50	1.80	0.059	0.071
e	0.95		0.037	
HE	2.60	3.00	0.102	0.118
L1	0.30	0.60	0.012	0.024
Lp	0.40	0.70	0.016	0.028
Q	0.20	0.30	0.008	0.012
x	-	0.10	-	0.004
y	-	0.10	-	0.004

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2	-	0.60	-	0.024
e1	2.10		0.083	
l1	-	0.90	-	0.035

Dimension in mm/inches